

CLAIM AMENDMENTS

Please amend the claims as described below. In accordance with 37 CFR §1.121, a complete listing of all claims in the application is provided below. Notably, the status of each claim is indicated in the parenthetical expression adjacent to the corresponding claim number.

Claims 1-31 (Cancelled).

- 1 **32. (Previously Presented)** An electromechanical device comprising:
 - 2 a substrate
 - 3 an insulation layer disposed on the substrate,
 - 4 a first semiconductor layer disposed on the insulation layer;
 - 5 an anchor that is disposed in an opening in the insulation layer and the first
 - 6 semiconductor layer and contacts the substrate, wherein the anchor includes a material
 - 7 that is different than the insulation layer;
 - 8 a second semiconductor layer, disposed on the anchor; and
 - 9 a fixed electrode, formed in part from the second semiconductor layer, wherein the
 - 10 fixed electrode is affixed to the substrate via the anchor.

- 1 **33. (Previously Presented)** The device of claim 32 wherein the anchor includes
- 2 silicon nitride, silicon carbide, germanium, silicon/germanium or gallium arsenide.

- 1 **34. (Previously Presented)** The device of claim 32 wherein the insulation layer
- 2 includes silicon nitride or silicon oxide.

1 **35. (Previously Presented)** The device of claim 32 further including a moveable
2 electrode, juxtaposed the fixed electrode, wherein the moveable electrode is formed in part
3 from the second semiconductor layer.

1 **36. (Currently Amended)** The device of claim 35 wherein the insulation layer is
2 comprised of includes silicon oxide and the anchor material includes silicon nitride, silicon
3 carbide, germanium, silicon/germanium or gallium arsenide.

1 **37. (Currently Amended)** The device of claim 35 wherein the insulation layer is
2 comprised of includes silicon oxide and the anchor material includes silicon, silicon carbide,
3 germanium, silicon/germanium, or gallium arsenide.

1 **38. (Currently Amended)** The device of claim 35 wherein the insulation layer is
2 comprised of includes silicon nitride and the anchor material includes silicon, silicon oxide,
3 silicon carbide, germanium, silicon/germanium or gallium arsenide.

1 **39. (Previously Presented)** The device of claim 32 wherein a substantial portion
2 of the fixed electrode overlying the anchor material is a monocrystalline silicon.

1 **40. (Previously Presented)** The device of claim 32 wherein a substantial portion
2 of the fixed electrode overlying the anchor material is a polycrystalline silicon.

1 **41. (Currently Amended)** The device of claim 32 further including:

2 a chamber, defined in part by including a first encapsulation layer having at least
3 one vent;
4 a moveable electrode disposed in the chamber and juxtaposed the fixed electrode;
5 a second encapsulation layer ~~comprised of a semiconductor material~~, deposited
6 over or in the vent, to thereby seal the chamber, wherein the second encapsulation layer
7 includes a semiconductor material.

1 42. (Currently Amended) The device of claim 41 wherein the second
2 encapsulation layer is ~~comprised of~~ includes polycrystalline silicon, porous polycrystalline
3 silicon, amorphous silicon, silicon carbide, silicon/germanium, germanium or gallium
4 arsenide.

1 43. (Currently Amended) The device of claim 42 wherein the first encapsulation
2 layer is ~~comprised of~~ includes polycrystalline silicon, porous polycrystalline silicon,
3 amorphous silicon, germanium, silicon/germanium, gallium arsenide, silicon nitride or
4 silicon carbide.

1 44. (Previously Presented) The device of claim 41 wherein:
2 the first encapsulation layer is a semiconductor material that is doped with a first
3 impurity to provide a first region of a first conductivity type, and
4 the semiconductor material of the second encapsulation layer is doped with a
5 second impurity to provide a second region with a second conductivity type and wherein
6 the first conductivity type is opposite the second conductivity type.

1 **45. (Currently Amended)** The device of claim 41 further including a contact having
2 at least a portion that is disposed outside the chamber.

1 **46. (Currently Amended)** The device of claim 41 wherein a first portion of the first
2 encapsulation layer is comprised of a monocrystalline silicon and a second portion of the
3 first encapsulation layer is comprised of a polycrystalline silicon.

1 **47. (Currently Amended)** The device of claim 41 wherein a first portion of the first
2 encapsulation layer is comprised of a monocrystalline silicon and a second portion of the
3 first encapsulation layer is comprised of a porous or amorphous silicon.

1 **48. (Previously Presented)** The device of claim 47 wherein the second
2 encapsulation layer overlying the second portion of the first encapsulation layer is a
3 polycrystalline silicon.

1 **49. (Currently Amended)** The device of claim 48 includes a field region disposed
2 outside and above the chamber wherein the field region is comprised of a monocrystalline
3 silicon.

1 **50. (Currently Amended)** An electromechanical device comprising:
2 a substrate
3 an insulation layer disposed on the substrate,
4 a first semiconductor layer disposed on the insulation layer;

5 an anchor that is disposed in an opening in the insulation layer and the first
6 semiconductor layer and contacts the substrate, wherein the anchor includes a material
7 that is different than the insulation layer;
8 a second semiconductor layer, disposed on the anchor; and
9 a fixed electrode, formed in part from the second semiconductor layer, wherein the
10 fixed electrode is affixed to the substrate via the anchor;
11 a moveable electrode, formed in part from the second semiconductor layer, wherein
12 the moveable electrode is disposed in a chamber wherein the chamber includes is defined
13 in part by a first encapsulation layer;
14 a second encapsulation layer comprised of a semiconductor material, deposited
15 over or in the vent, to thereby seal the chamber, wherein the second encapsulation layer
16 includes a semiconductor material;
17 a contact; and
18 a trench, disposed around at least a portion of the contact, wherein the contact and
19 the trench as is disposed outside the chamber and wherein the trench includes a first
20 material disposed therein to electrically isolate the contact.

1 51. (Currently Amended) The device of claim 50 wherein the second
2 encapsulation layer is comprised of includes polycrystalline silicon, porous polycrystalline
3 silicon, amorphous silicon, silicon carbide, silicon/germanium, germanium, or gallium
4 arsenide.

1 **52. (Currently Amended)** The device of claim 51 wherein the first encapsulation
2 layer is comprised of includes polycrystalline silicon, porous polycrystalline silicon,
3 amorphous silicon, germanium, silicon/germanium, gallium arsenide, silicon nitride or
4 silicon carbide.

1 **53. (Currently Amended)** The device of claim 50 wherein the first material is an
2 insulating material is disposed on at least the outer surfaces of the trench.

1 **54. (Previously Presented)** The device of claim 53 wherein the trench includes a
2 second material surrounded by the first material and wherein the second material is a
3 semiconductor material.

1 **55. (Previously Presented)** The device of claim 53 wherein the trench is disposed
2 on an etch stop region.

1 **56. (Previously Presented)** The device of claim 53 wherein the etch stop region is
2 a silicon nitride or silicon dioxide.

1 **57. (Previously Presented)** The device of claim 53 wherein the first material is a
2 silicon nitride or silicon dioxide.

1 **58. (Previously Presented)** The device of claim 53 wherein the trench surrounds
2 the contact.

1 **59. (Previously Presented)** The device of claim 50 wherein the anchor includes
2 silicon nitride, silicon carbide, germanium, silicon/germanium or gallium arsenide.

1 **60. (Previously Presented)** The device of claim 50 wherein the insulation layer
2 includes silicon nitride or silicon oxide.

1 **61. (Currently Amended)** The device of claim 50 wherein the insulation layer
2 includes is comprised of silicon oxide and the anchor material includes silicon nitride,
3 silicon carbide, germanium, silicon/germanium or gallium arsenide.

1 **62.. (Currently Amended)** The device of claim 50 wherein the insulation layer
2 includes is comprised of silicon nitride and the anchor material includes silicon, silicon
3 oxide, silicon carbide, germanium, silicon/germanium or gallium arsenide.

1 **63. (Previously Presented)** The device of claim 50 wherein a substantial portion
2 of the fixed electrode overlying the anchor material is a monocrystalline silicon.

1 **64. (Previously Presented)** The device of claim 50 wherein a substantial portion
2 of the fixed electrode overlying the anchor material is a polycrystalline silicon.